

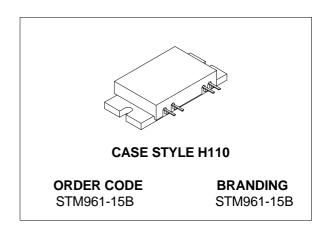
# STM961-15B

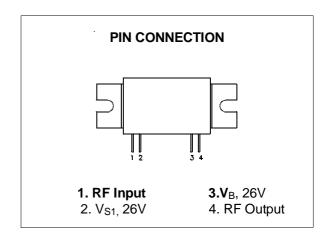
# RF POWER MODULE DIGITAL CELLULAR APPLICATIONS

- LINEAR POWER AMPLIFIER
- 915-960 MHz
- 26 VOLTS
- INPUT/OUTPUT 50 OHMS
- POUT = 42 dBm CW or PEP
- GAIN = 30 dB

#### **DESCRIPTION**

The STM961-15B module is designed for digital cellular radio base station applications in the 915-960 MHz frequency range operating at 26V. The STM961-15B is designed to meet the low distortion, high linearity requirements of modern digital cellular base station equipment.





### ABSOLUTE MAXIMUM RATINGS (Tcase = 85 °C)

Symbol	Parameter	Value	Unit
$V_{S1}$ , $V_{S2}$	DC Supply Voltage	28	Vdc
$V_B$	DC Bias Voltage	28	Vdc
P <sub>IN</sub>	RF Input Power	14	dBm CW
Pout	RF Output Power (V = 26V)	43	dBm CW
T <sub>STG</sub>	Storage Temperature	- 30 to + 100	°C

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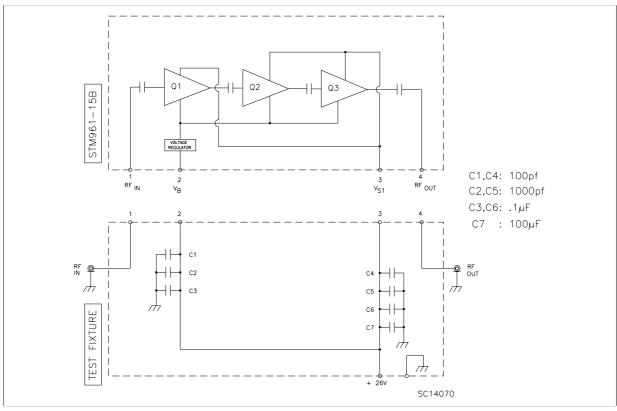
# **ELECTRICAL SPECIFICATION** ( $T_{case} = -10$ °C to +85 °C, $V_{S1} = 26$ V, $V_B = 26$ V to 27 V)

### **DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
BW	Frequency Range		915		960	MHz	
G <sub>P</sub>	Power Gain	P <sub>OUT</sub> = +42 dBm CW	28	30		dB	
h	Efficiency	P <sub>OUT</sub> = +42 dBm CW	32	35		%	
	VSWR	$P_{OUT}$ = +42 dBm CW $Z_{S}$ , $Z_{L}$ = 50 $\Omega$			2:1	VSWR	
$I_Q$	Quiescent Current	$P_{IN} = 0 dBm$		580		mA	
2F <sub>O</sub>	Harmonics	P <sub>OUT</sub> = +42 dBm CW			-30	dBc	
3F <sub>O</sub>	Harmonics	P <sub>OUT</sub> = +42 dBm CW			-50	dBc	
F	Gain Flatness	P <sub>OUT</sub> = +42 dBm CW		1		dB	
$P_{1dB}$	Output Power @ 1 dB Compression		41			dBm	
	Load Mismatch	VSWR = 3:1 P <sub>OUT</sub> = +42 dBm CW	No Degradation in Output Power		utput		
	Stability			•	us Outputs more b Below Carrier		

REF. 1017332I

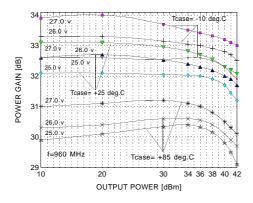
### MODULE DC AND TEST FIXTURE CONFIGURATION



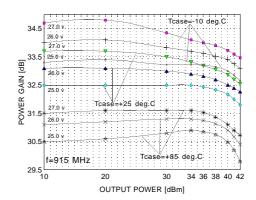
REF. 1014532D

#### TYPICAL PERFORMANCE

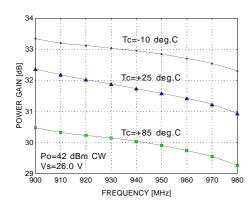
### Power Gain vs Output Power



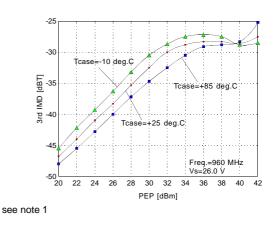
#### Power Gain vs Output Power



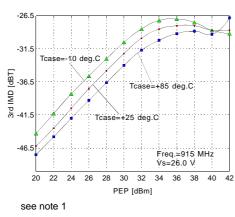
#### Power Gain vs Frequency & Temperature



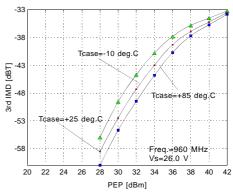
3rd Order IMD vs Output Power & Temperature



3rd Order IMD vs Output Power & Temperature



5th Order IMD vs Output Power & Temperature



see note 1

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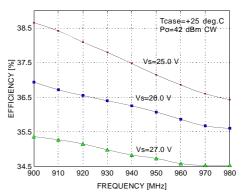
#### TYPICAL PERFORMANCE

### 5th Order IMD vs Output Power & Temperature

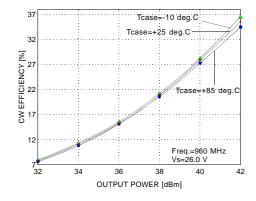
#### -33 -38 Tcase=-10 deg.C 3rd IMD [dBT] =+25 deg.C Tcase=+85 deg.C -53 -58 Freq.=915 MHz Vs=26.0 V 22 24 26 28 30 32 34 36 38 40 PEP [dBm]

see note 1

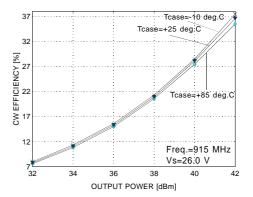
Efficiency vs Frequency



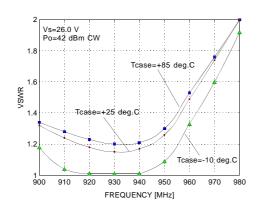
CW Efficiency vs Output Power & Temperature



CW Efficiency vs Output Power & Temperature



VSWR vs Frequency & Temperature



Note (1): Two-tone test; 20KHz separation; IMD (in dBT) is referenced to the individual tone level.

#### APPLICATIONS RECOMMENDATIONS

#### **OPERATION LIMITS**

The STM961-15B power module should never be operated under any condition which exceeds the Absolute Maximum Ratings presented on this data sheet. Nor should the module be operated continuously at any of the specified maximum ratings. If the module is to be subjected to one or more of the maximum rating conditions, care must be taken to monitor other parameters which may be affected.

#### **DECOUPLING**

Failure to properly decouple any of the voltage supply pins will result in oscillations at certain operating frequencies. Therefore, it is recommended that these pins be bypassed as indicated in the Module DC and Test Fixture Configuration drawing of this data sheet.

#### **MODULE MOUNTING**

To insure adequate thermal transfer from the module to the heatsink, it is recommended that a satisfactory thermal compound such as Dow Corning 340, Wakefield 120-2 or equivalent be applied between the module flange and the heatsink.

The heatsink mounting surface under the module should be flat to within  $\pm$  0.05mm ( $\pm$  0.002 inch). The module should be mounted to the heatsink using 3.5 mm (or 6-32) or equivalent screws torqued to 5-6 kg-cm (4-6 in-lb).

The module leads should be attached to equipment PC board using 180°C solder applied to the leads with a properly grounded soldering iron tip, not to exceed 195°C, applied a minimum of 2 mm (0.080 inch) from the body of the module for a duration not to exceed 15 seconds per lead. It is imperative that no other portion of the module, other than the leads, be subjected to temperatures in excess of 100°C (maximum storage temperature), for any period of time, as the plastic moulded cover, internal components and sealing adhesives may be adversely affected by such conditions.

Due to the construction techniques and materials used within the module, reflow soldering of the flange heatsink or leads, is not recommended.

#### THERMAL CONSIDERATIONS

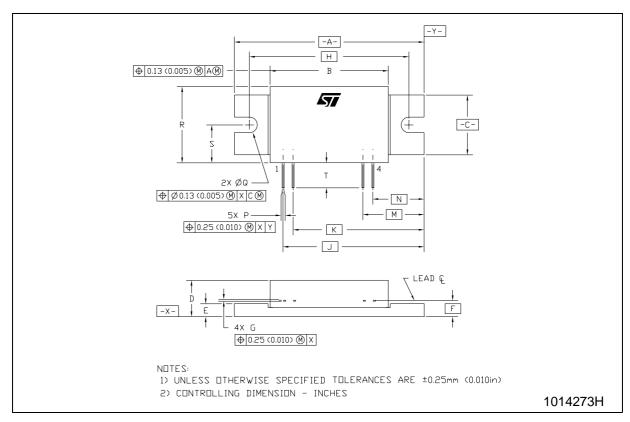
It will be necessary to provide a suitable heatsink in order to maintain the module flange temperature at or below to maximum case operating temperature. In a case where the module output power limited to +42 dBm CW and designing for the worst case efficiency of 32%, the power dissipated by the module will be 33.6 Watts. The heatsink must be designed such that the thermal rise will be less than the difference between the maximum operating case temperature of the module while dissipating 33.6 W.

At  $T_{case} = +85$  °C, V = 26V,  $Z_{L} = 50 \Omega$  and  $P_{OUT} = 42$  dBm, maximum junction temperatures for the individual transistors should be below the following values:

 $Q1 = 140 \,^{\circ}C$ ,  $Q2 = 145 \,^{\circ}C$ ,  $Q3 = 130 \,^{\circ}C$ .

## **H110 MECHANICAL DATA**

DIM.	mm			inch		
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	48.01		48.51	1.890		1.910
В	29.72		30.22	1.170		1.190
С	15.12		15.49	0.595		0.610
D	8.89		9.55	0.350		0.376
Е	3.05		3.42	0.120		0.135
F		4.06			0.160	
G	0.13		0.38	0.005		0.015
Н		40.64			1.600	
J		35.94			1.415	
К		33.40			1.315	
М		15.62			0.615	
N		13.08			0.515	
Р	0.38		0.63	0.015		0.025
Q	3.81		4.06	0.150		0.160
R	17.40		19.55	0.685		0.770
S	8.77	·	9.77	0.345		0.385
Т	4.52		5.72	0.178		0.225



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